ESJM06 2.0A 6.0kV --nS

High Current High Voltage Silicon Rectifier Diodes

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High Current,Low Forward Voltage.
3. Avalanche Characteristic.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. Rectifier for high voltage power supply.
2. High voltage transformer rectifier.
3. Doubler rectifier circuit.
4. Accelerator power supply.

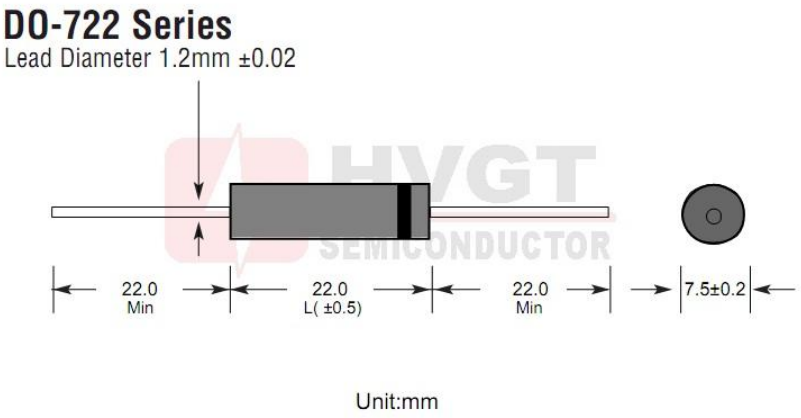
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.55 grams (approx).

SHAPE DISPLAY:

RoHS COMPLIANT

SIZE: (Unit:mm) HVGT NAME: DO-722



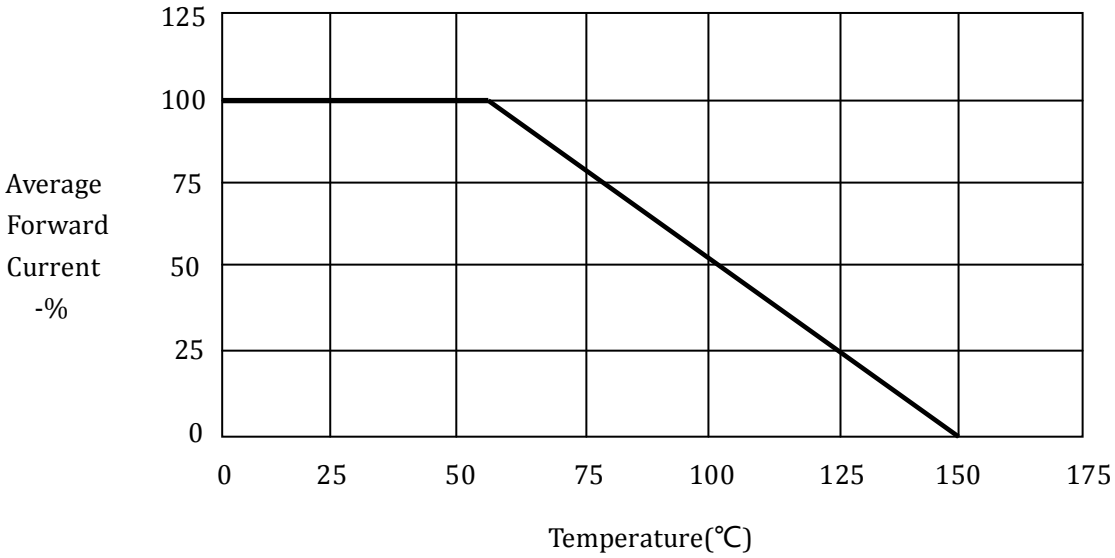
MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Renerse Voltage	V_{RRM}	T_A=25°C	6.0	kV
Non-Repetitive Peak Renerse Voltage	V_{RSM}	T_A=25°C	--	kV
Average Forward Current Maximum	I_{FAVM}	T_A=55°C	2.0	A
		T_{OIL}=55°C	--	A
Non-Repetitive Forward Surge Current	I_{FSM}	T_A=25°C; 60Hz Half-Sine Wave; 8.3mS	60	A
Junction Temperature	T_J		150	°C
Allowable Operation Case Temperature	Tc		-40~+150	°C
Storage Temperature	T_{STG}		-55~+175	°C

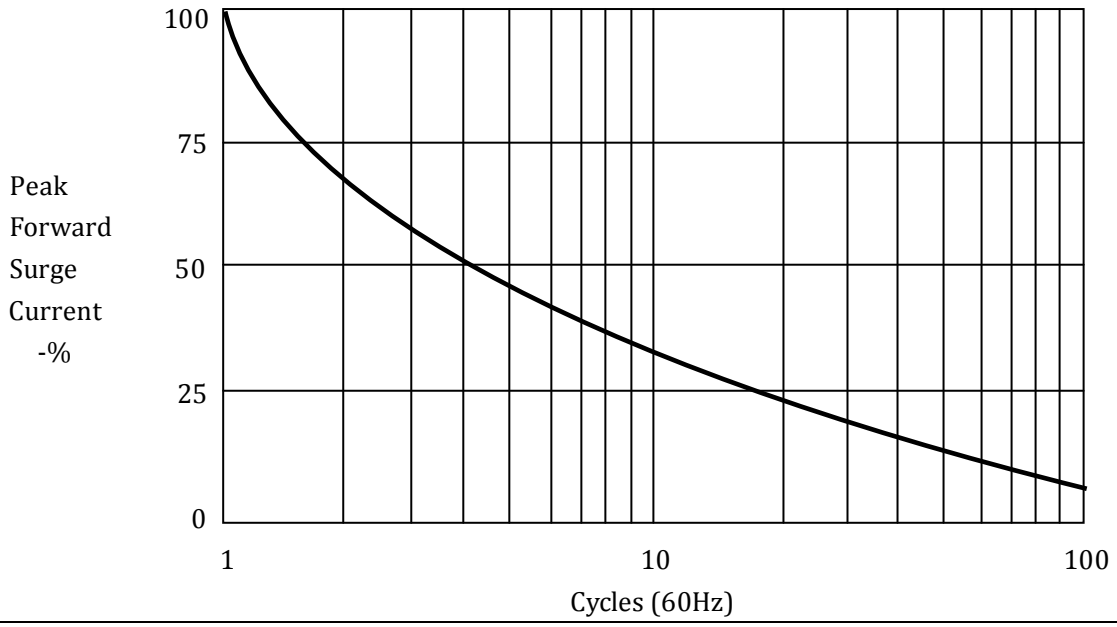
ELECTRICAL CHARACTERISTICS: T_A=25°C (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at 25°C; at I_{FAVM}	5.4	V
Maximum Reverse Current	I_{R1}	at 25°C; at V_{RRM}	2.0	uA
	I_{R2}	at 100°C; at V_{RRM}	10	uA
Maximum Reverse Recovery Time	T_{RR}	at 25°C; I_F=0.5I_R; I_R=I_{FAVM}; I_{RR}=0.25I_R	--	nS
Junction Capacitance	C_J	at 25°C; V_R=0V; f=1MHz	--	pF

Forward Current Derating Curves



Non-Repetitive Surge Current



Marking	Type	Code	Cathode Mark
	ESJM06	ESJM06 HVGT	